

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error
1	BRS	189	sti with gate near (oxide or dielectric or insulating) with semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 21:06		0
2	BRS	7	sti with gate near (oxide or dielectric or insulating) with semiconductor and gate near electrode with semiconductor with pattern\$6 and drain and source and ion near implant\$6 and (((thermal or heat) with treat\$6) or anneal\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/02 19:55		0
3	BRS	46	sti with gate near (oxide or dielectric or insulating) with semiconductor and resistan\$6 with region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/02 19:59		0
4	BRS	5	sti with gate near (oxide or dielectric or insulating) with semiconductor and resistan\$6 with region and semiconductor with electrode with pattern\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/02 20:00		0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error
5	BRS	16	sti with gate near (oxide or dielectric or insulating) with semiconductor and resistanc\$6 with region and semiconductor with electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/02 20:00		0
6	BRS	11	sti with gate near (oxide or dielectric or insulating) with semiconductor and gate near electrode with semiconductor with pattern\$6 and drain and source and ion near implant\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/02 20:01		0
7	BRS	19	sti with gate near (oxide or dielectric or insulating) with semiconductor and gate near electrode with semiconductor with pattern\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/02 20:01		0
8	BRS	84	sti with resist\$7 and gate near (oxide or dielectric or insulating) with semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/05 17:25		0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Errors
9	BRS	55	sti with resist\$7 and gate near (oxide or dielectric or insulating) with semiconductor and mask with resist\$7	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/05 17:26		0
10	BRS	45	sti with resist\$7 and gate near (oxide or dielectric or insulating) with semiconductor and mask with resist\$7 and ion with implant\$7	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/05 17:27		0
11	BRS	12	sti with resist\$7 and gate near (oxide or dielectric or insulating) with semiconductor and mask with resist\$7 and ion with implant\$7 and spacer with resist\$7	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/07 14:42		0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Errors
12	BRS	6	sti with (resista\$7 or resisto\$6) and gate near (oxide or dielectric or insulating) with semiconductor and mask with resist\$7 and ion with implant\$7 and spacer with (resisto\$7 or resista\$7)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/07 14:47		0
13	BRS	26	(isolat\$6 or field adj oxide) with (resista\$7 or resisto\$6) and gate near (oxide or dielectric or insulating) with semiconductor and mask with resist\$7 and ion with implant\$7 and spacer with (resisto\$7 or resista\$7)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/07 14:49		0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Errors
14	BRS	24	(isolat\$6 or field adj oxide) with (resista\$7 or resisto\$6) and gate near (oxide or dielectric or insulating) with semiconductor and mask with (resisto\$7 or resista\$6) and ion with implant\$7 and spacer with (resisto\$7 or resista\$7)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/07 16:16		0
15	BRS	30	(isolat\$6 or field adj oxide) with (resista\$7 or resisto\$6) and gate with mask with (resisto\$7 or resista\$6) and ion with implant\$7 and spacer with (resisto\$7 or resista\$7) and source and drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/07 16:17		0
16	BRS	25	5013678.URPN.	USPAT	2004/05/07 16:50		0
17	BRS	15	5585302.URPN.	USPAT	2004/05/07 17:03		0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error	Info
18	BRS	341	implant with resistance with (source or drain) and (field adj oxide or isolat\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 21:07			0
19	BRS	2371	implant\$6 with resist\$6 with (source or drain) and (field adj oxide or isolat\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 21:09			0
20	BRS	1130	implant\$6 with (resista\$6 or resisto\$6) with (source or drain) and (field adj oxide or isolat\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 21:11			0
21	BRS	322	implant\$6 with (resista\$6 or resisto\$6) with (source or drain) and (field adj oxide or isolat\$6) and (mask or photoresist) with (resista\$6 or resisto\$6)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 21:12			0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error
22	BRS	134	implant\$6 with (resista\$6 or resisto\$6) with (source or drain) and (field adj oxide or isolat\$6) and (mask or photoresist) with (resista\$6 or resisto\$6) and ldd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 21:14		0
23	BRS	75	implant\$6 with (resista\$6 or resisto\$6) with (source or drain) and (field adj oxide or isolat\$6) and implant\$6 with (mask or photoresist) with (resista\$6 or resisto\$6) and ldd	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 21:15		0

	Type	Hits	Search Text	DBs	Time Stamp	Comments	Error	Ratio
24	BRS	31	implant\$6 with (resista\$6 or resisto\$6) with (source or drain) and (field adj oxide or isolat\$6) and implant\$6 with (mask or photoresist) with (resista\$6 or resisto\$6) and ldd and (heat\$6 or thermal or anneal\$6) with activat\$6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 23:10			0
25	IS& R	2	("20020127791").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/06/24 23:10			0